

29. A process according to claim 28, wherein said step of bonding comprises bonding with an organic die-bonding film further having a residual volatile component in an amount of not more than 3.0% by weight.

30. A process according to claim 29, wherein said step of bonding comprises bonding with an organic die-bonding film further having a saturation moisture absorption of 1.0% by volume or less.

31. A process according to claim 30, wherein said step of bonding comprises bonding with an organic die-bonding film further having a void volume of 10% or less in terms of voids present in the material and at an interface between said film and said support at a stage where the semiconductor has been bonded to the support member by the film.

32. A process according to claim 31, further comprising the step of: encapsulating the bonded chip to produce the semiconductor device.

33. A process according to claim 25, wherein said die-bonding material is a film comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin.

34. A process according to claim 31, wherein said die-bonding material is a film comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin.

35. A process according to claim 32, wherein said die-bonding material is a film comprising one or more resins selected from the group consisting of silicone resin, acrylic resin, polyimide resin and epoxy resin.

36. A process according to claim 25, wherein said die-bonding material is a film comprising a polyimide resin and epoxy resin.

37. A process according to claim 31, wherein said die-bonding material is a film comprising a polyimide resin and epoxy resin.

38. A process according to claim 32, , wherein said die-bonding material is a film comprising a polyimide resin and epoxy resin.

39. A process according to claim 25, wherein said die-bonding material is a film comprising an acrylic resin and epoxy resin.

40. A process according to claim 31, wherein said die-bonding material is a film comprising an acrylic resin and epoxy resin.

41. A process according to claim 32, wherein said die-bonding material is a film comprising an acrylic resin and epoxy resin.

42. A process according to claim 25, wherein said die-bonding material is a film comprising a silicone resin.

43. A process according to claim 31, wherein said die-bonding material is a film comprising a silicone resin.

44. A process according to claim 32, wherein said die-bonding material is a film comprising a silicone resin.

45. A process according to claim 25, wherein said die-bonding material is a film comprising a silicone resin and epoxy resin.

46. A process according to claim 31, wherein said die-bonding material is a film comprising a silicone resin and epoxy resin.

47. A process according to claim 32, wherein said die-bonding material is a film comprising a silicone resin and epoxy resin.

48. A process according to claim 36, wherein the polyimide is a polyimide synthesized from a combination which is selected from the group consisting of a

combination of 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane; a combination of 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenylether; a combination of 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane; a combination of 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl] propane; a combination of a mixture of 1,2-(ethylene)bis(trimellitate anhydride) and 1,10-(decamethylene)bis(trimellitate anhydride) being the same mol as the mixture and 2,2-bis[4-(4-aminophenoxy)phenyl] propane; and a combination of 1,10-(decamethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

49. A process according to claim 25, wherein said step of bonding is carried out with a bonding time of from 0.1 seconds (inclusive) to 2 seconds.

50. A process according to claim 31, wherein said step of bonding is carried out with a bonding time of from 0.1 seconds (inclusive) to 2 seconds.

51. A process according to claim 32, wherein said step of bonding is carried out with a bonding time of from 0.1 seconds (inclusive) to 2 seconds.

52. A process according to claim 25, wherein said step of bonding is carried out with a bonding time of from 0.1 seconds (inclusive) to 1.5 seconds.

53. A process according to claim 31, wherein said step of bonding is carried out with a bonding time of from 0.1 seconds (inclusive) to 1.5 seconds.

54. A process according to claim 32, wherein said step of bonding is carried out with a bonding time of from 0.1 seconds (inclusive) to 1.5 seconds.

55. A process according to claim 25, wherein said step of bonding is carried out at a pressure of 0.1-4 gf/mm².

56. A process according to claim 31, wherein said step of bonding is carried out at a pressure of 0.1-4 gf/mm².

57. A process according to claim 32, wherein said step of bonding is carried out at a pressure of 0.1-4 gf/mm².

58. A process according to claim 49, wherein said step of bonding is carried out at a pressure of 0.1-4 gf/mm².

59. A process according to claim 52, wherein said step of bonding is carried out at a pressure of 0.1-4 gf/mm².

60. A process according to claim 25, wherein said step of bonding is carried out at a pressure of 0.3-2 gf/mm².

61. A process according to claim 31, wherein said step of bonding is carried out at a pressure of 0.3-2 gf/mm².

62. A process according to claim 32, wherein said step of bonding is carried out at a pressure of 0.3-2 gf/mm².

63. A process according to claim 49, wherein said step of bonding is carried out at a pressure of 0.3-2 gf/mm².

64. A process according to claim 52, wherein said step of bonding is carried out at a pressure of 0.3-2 gf/mm².

65. A semiconductor device made by the process of claim 25. --

REMARKS

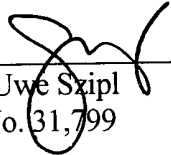
With the above amendments, the specification has been amended to identify and incorporate by reference the parent application, i.e., Serial No. 08/981,702, as well as the international application and Japanese application upon which the present application claims priority.

Additionally, all of the claims originally filed with the parent application, i.e., claims 1-24, have been cancelled and new claims 25-65 have been inserted for prosecution in this continuation application.

Accordingly, it is believed that this application is in good condition for examination, and the Examiner's early and favorable action is respectfully solicited. Questions are welcomed by the below-signed attorney for applicants.

Respectfully submitted,

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